

N-Ch 60V Fast Switching MOSFETs

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

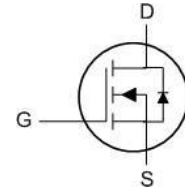
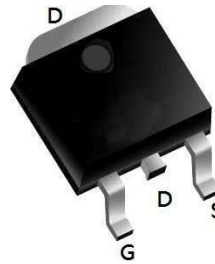
- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Product Summary



BVDSS	RDSON	ID
60V	4mΩ	120A

TO252-3L Pin Configuration



Absolute Maximum Ratings:

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C=25^{\circ}\text{C}$	I_D	120	A
	$T_C=100^{\circ}\text{C}$		57	
Pulsed Drain Current ¹		I_{DM}	360	A
Single Pulse Avalanche Energy ²		EAS	135.2	mJ
Total Power Dissipation	$T_C=25^{\circ}\text{C}$	P_D	71.4	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient ³	$R_{\theta JA}$	58	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	1.75	°C/W

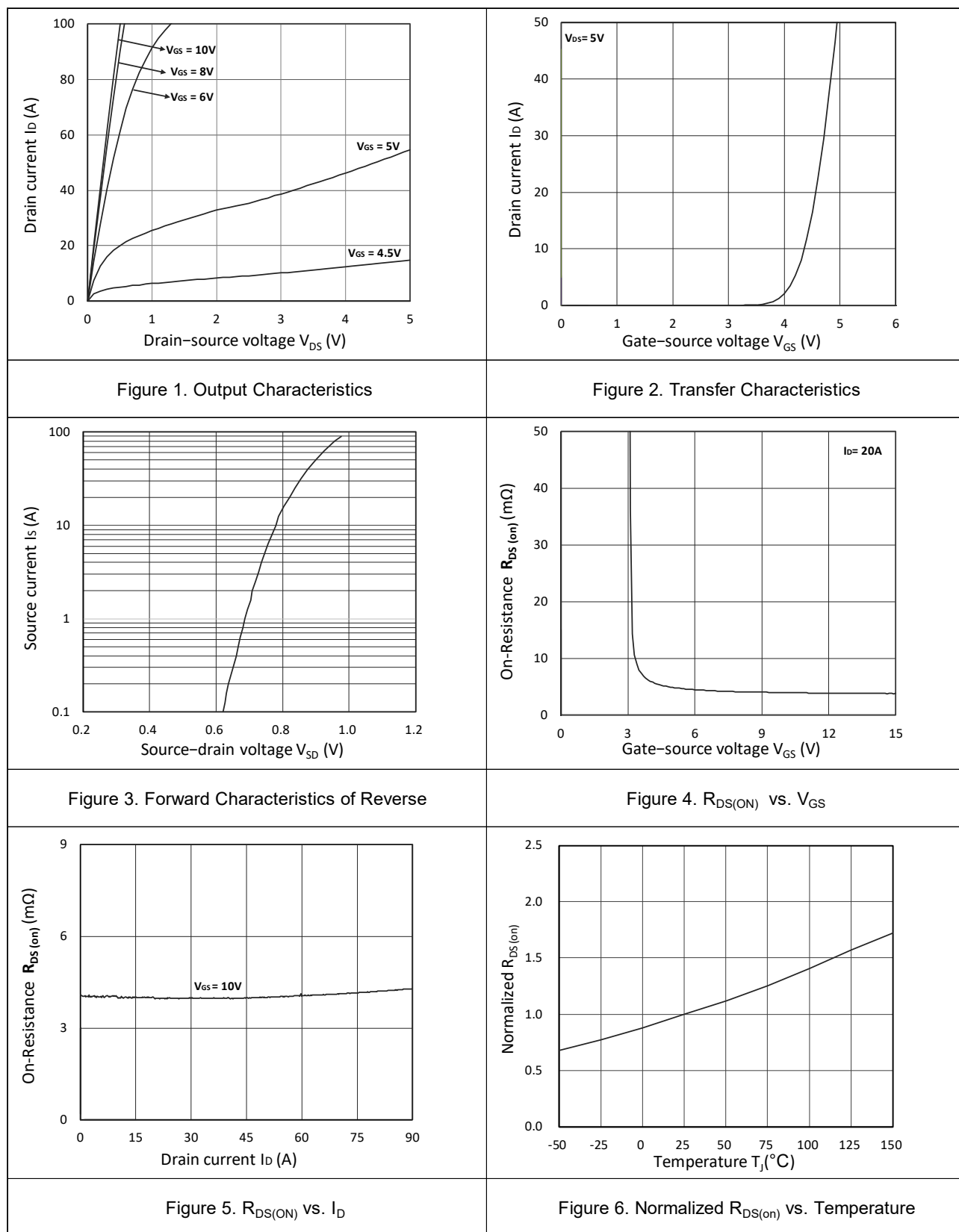
Electrical Characteristics ($T_J = 25^\circ\text{C}$, unless otherwise noted)

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60	-	-	V
Gate-body Leakage Current		I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T _J =25°C	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V	-	-	1	μA
	T _J =100°C			-	-	100	
Gate-Threshold Voltage		V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.5	2.9	3.5	V
Drain-Source On-Resistance ⁴		R _{DS(on)}	V _{GS} = 10V, I _D = 20A	-	4	5.2	mΩ
Forward Transconductance ⁴		g _{fs}	V _{DS} = 10V, I _D = 20A	-	89	-	S
Dynamic Characteristics ⁵							
Input Capacitance		C _{iss}	V _{DS} = 30V, V _{GS} =0V, f =1MHz	-	1673	-	pF
Output Capacitance		C _{oss}		-	773	-	
Reverse Transfer Capacitance		C _{rss}		-	46.8	-	
Gate Resistance		R _g	f = 1MHz	-	1.8	-	Ω
Switching Characteristics ⁵							
Total Gate Charge		Q _g	V _{GS} = 10V, V _{DS} = 30V, I _D = 20A	-	28.5	-	nC
Gate-Source Charge		Q _{gs}		-	7.8	-	
Gate-Drain Charge		Q _{gd}		-	8.4	-	
Turn-On Delay Time		t _{d(on)}	V _{GS} =10V, V _{DD} = 30V, R _G = 3Ω, I _D = 20A	-	11.2	-	ns
Rise Time		t _r		-	8.2	-	
Turn-Off Delay Time		t _{d(off)}		-	19.6	-	
Fall Time		t _f		-	6.2	-	
Body Diode Reverse Recovery Time		t _{rr}	I _F =20A, dI/dt=100A/μs	-	50	-	ns
Body Diode Reverse Recovery Charge		Q _{rr}		-	20	-	nC
Drain-Source Body Diode Characteristics							
Diode Forward Voltage ⁴		V _{SD}	I _S = 20A, V _{GS} = 0V	-	-	1.2	V
Continuous Source Current	T _C =25°C	I _S	-	-	-	120	A

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)} = 150^\circ\text{C}$.
2. The EAS data shows Max. rating. The test condition is $V_{DD} = 25V, V_{GS} = 10V, L = 0.4\text{mH}, I_{AS} = 26A$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Characteristics



N-Ch 60V Fast Switching MOSFETs

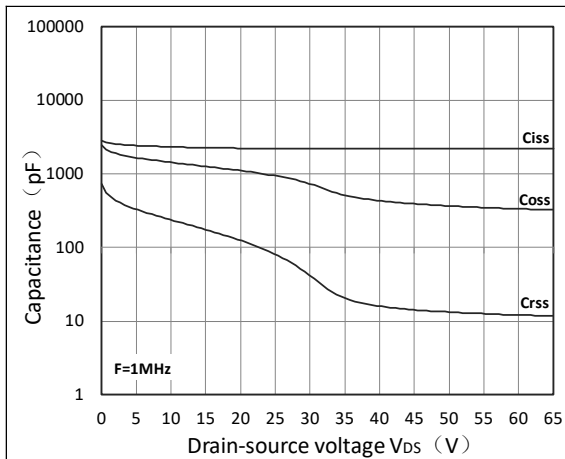


Figure 7. Capacitance Characteristics

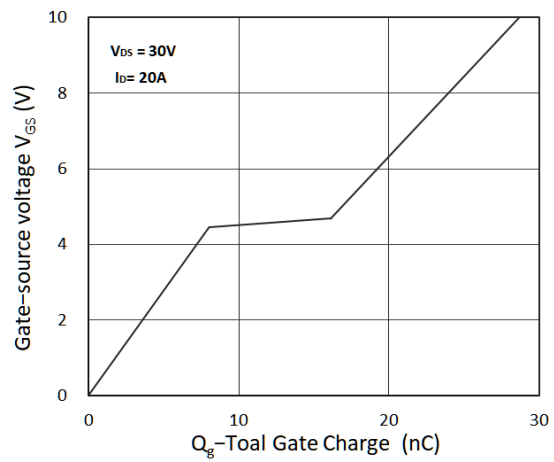


Figure 8. Gate Charge Characteristics

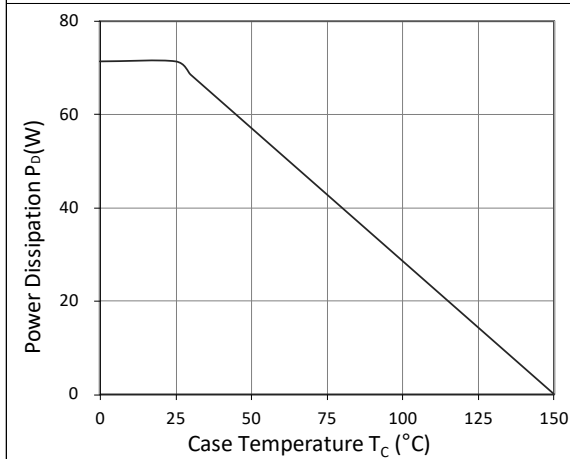


Figure 9. Power Dissipation

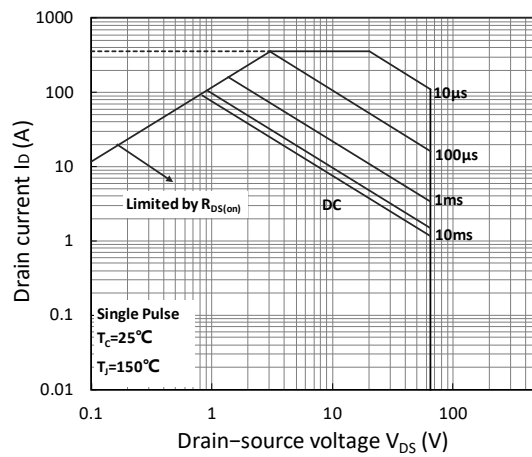


Figure 10. Safe Operating Area

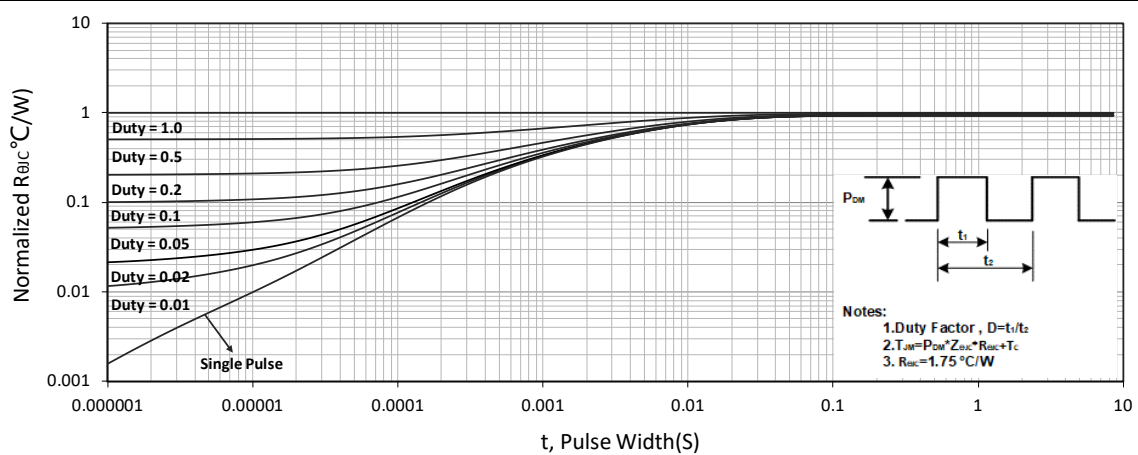


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

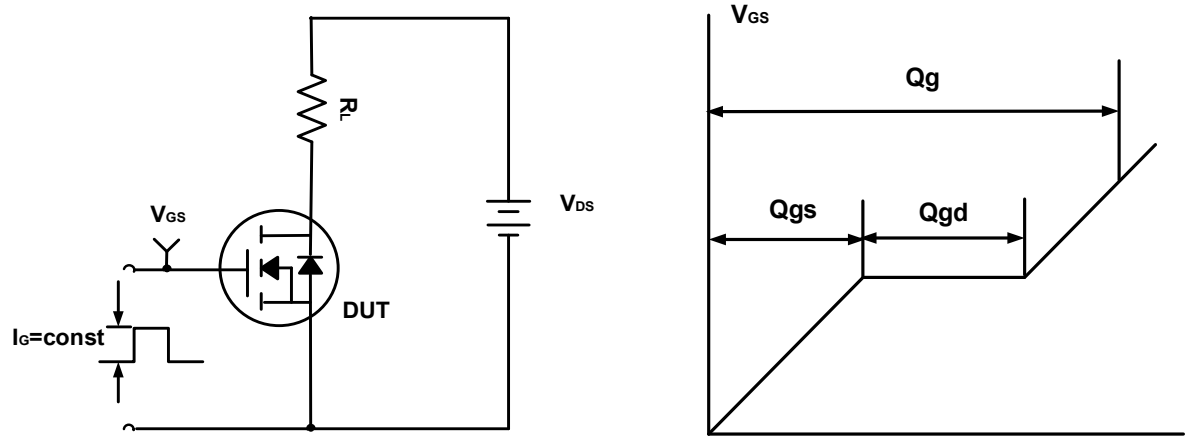


Figure A. Gate Charge Test Circuit & Waveforms

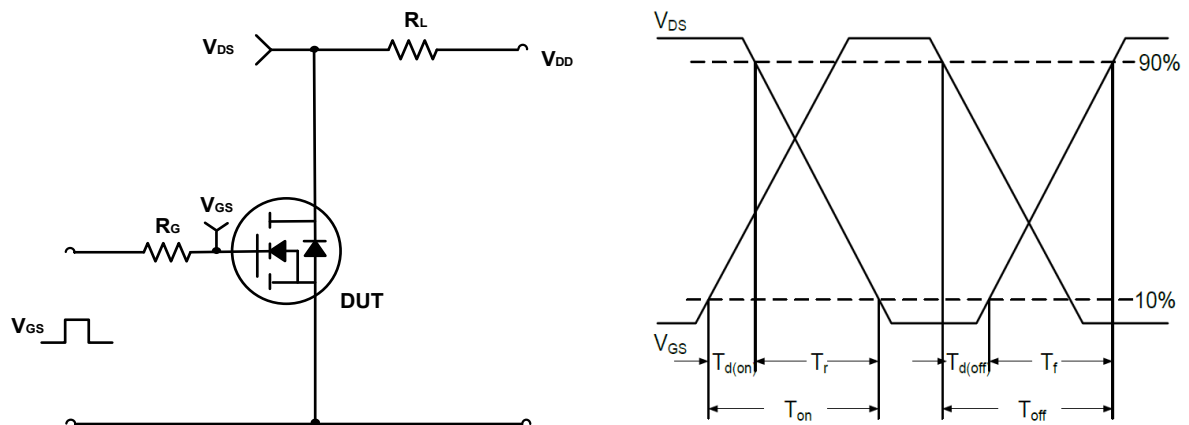


Figure B. Switching Test Circuit & Waveforms

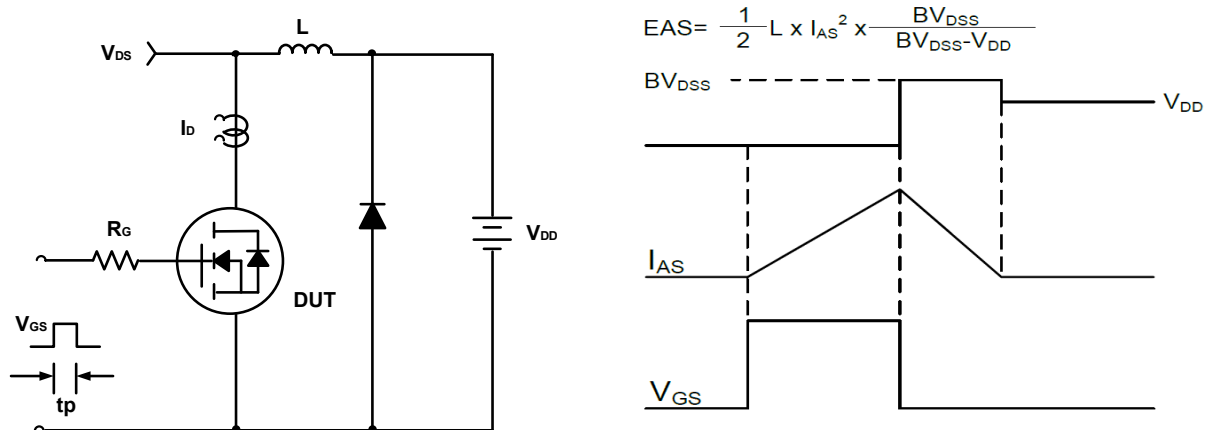
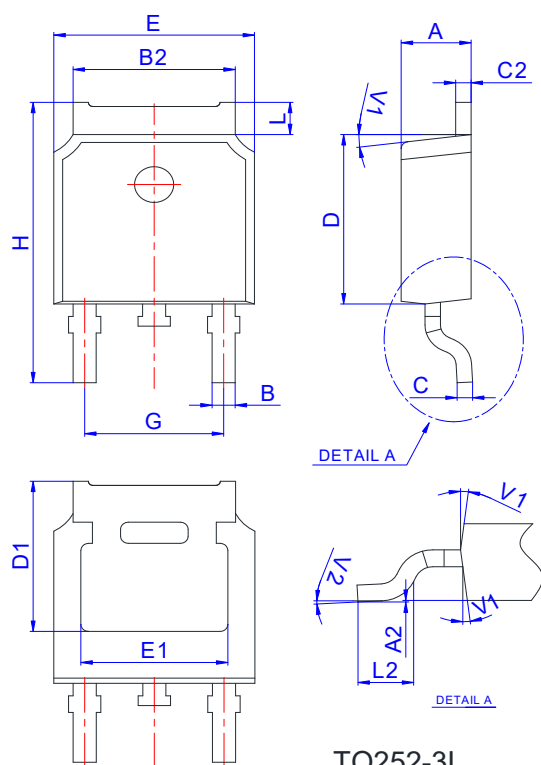


Figure C. Unclamped Inductive Switching Circuit & Waveforms

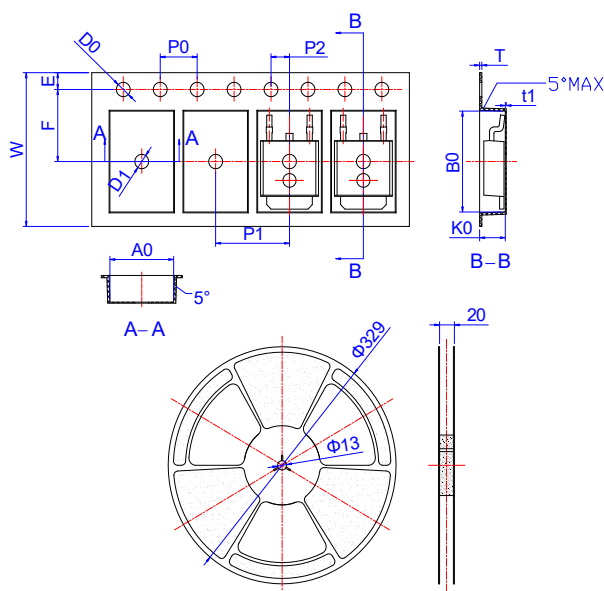
Package Mechanical Data-TO252-3L



TO252-3L

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583